

CMPT3646

**SURFACE MOUNT
NPN SILICON TRANSISTOR**



SOT-23 CASE



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT3646 type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for ultra high speed switching applications.

MARKING CODE: C2R

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO} 40
 V_{CES} 40
 V_{CEO} 15
 V_{EBO} 5.0
 I_C 200
 P_D 350
 T_J, T_{stg} -65 to +150
 Θ_{JA} 357

UNITS

V
V
V
V
mA
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	$V_{CE}=20\text{V}$		0.5	μA
I_{CES}	$V_{CE}=20\text{V}, T_A=65^\circ\text{C}$		3.0	μA
BV_{CBO}	$I_C=100\mu\text{A}$	40		V
BV_{CES}	$I_C=10\mu\text{A}$	40		V
BV_{CEO}	$I_C=10\text{mA}$	15		V
BV_{EBO}	$I_E=100\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$		0.20	V
$V_{CE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}, T_A=65^\circ\text{C}$		0.30	V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		0.28	V
$V_{CE(SAT)}$	$I_C=300\text{mA}, I_B=30\text{mA}$		0.50	V
$V_{BE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$	0.75	0.95	V
$V_{BE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.20	V
$V_{BE(SAT)}$	$I_C=300\text{mA}, I_B=30\text{mA}$		1.70	V
h_{FE}	$V_{CE}=0.4\text{V}, I_C=30\text{mA}$	30	120	
h_{FE}	$V_{CE}=0.5\text{V}, I_C=100\text{mA}$	25		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=300\text{mA}$	15		

R3 (1-February 2010)

CMPT3646

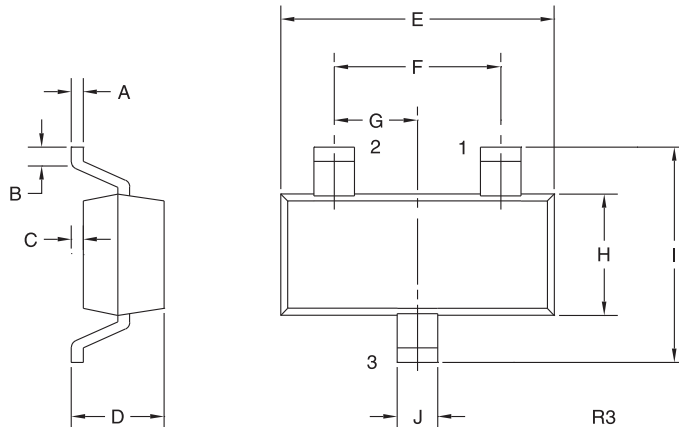
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=10\text{V}$, $I_C=30\text{mA}$, $f=100\text{MHz}$	350		MHz
C_{ob}	$V_{CB}=5.0\text{V}$, $I_E=0$, $f=1.0\text{MHz}$		5.0	pF
C_{ib}	$V_{BE}=0.5\text{V}$, $I_C=0$, $f=1.0\text{MHz}$		8.0	pF
t_{on}	$V_{CC}=10\text{V}$, $I_C=300\text{mA}$, $I_{B1}=30\text{mA}$		18	ns
t_{off}	$V_{CC}=10\text{V}$, $I_C=300\text{mA}$, $I_{B1}=I_{B2}=30\text{mA}$		28	ns
t_s	$V_{CC}=10\text{V}$, $I_C=I_{B1}=I_{B2}=10\text{mA}$		18	ns

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODE: C2R

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R3 (1-February 2010)